

### CLAIMS

1. (previously presented) A chemical mechanical polishing (CMP) pad, comprising:

- a unitary body having a first side and a second side, said second side being a polishing side;
- said first side having a plurality of holes formed therein, arranged into a concentric circular configuration; and
- said second side having a plurality of grooves formed therein, arranged into a concentric circular configuration;

wherein each of said plurality of holes in said first side is aligned with one of said plurality of grooves in said second side;

the depth of each of said plurality of holes extends up to said one of said plurality of grooves; and

each of said holes are sized in a manner so as not to exceed the width of a corresponding groove aligned therewith.

2-8. (canceled)

9. (previously presented) A chemical mechanical polishing (CMP) pad assembly, comprising:

- a sub pad attached to the upper surface of a support turntable;
- a CMP pad having unitary body with a first side and a second side, said second side being a polishing side, wherein said first side is in contact with said sub pad;
- said first side having a plurality of holes formed therein, arranged into a concentric circular configuration; and
- said second side having a plurality of grooves formed therein, arranged into a concentric circular configuration.

wherein each of said plurality of holes in said first side is aligned with one

of said plurality of grooves in said second side;

the depth of each of said plurality of holes extends up to said one of said plurality of grooves; and

each of said holes are sized in a manner so as not to exceed the width of a corresponding groove aligned therewith.

10-16. (canceled)

17. (previously presented) A chemical mechanical polishing (CMP) assembly, comprising:

a rotatable pressure block for securing a semiconductor wafer therein;

a support turntable having a sub pad attached to the upper surface thereof;

a CMP pad having unitary body with a first side and a second side,

wherein said first side is in contact with said sub pad and said second side is disposed so as to come into contact with said semiconductor wafer during a polishing operation; and

at least one supply line for dispensing CMP fluid for said polishing operation;

wherein said first side of said CMP pad has a plurality of holes formed therein, arranged into a concentric circular configuration, and said second side of said CMP pad has a plurality of grooves formed therein, arranged into a concentric circular configuration; and

wherein each of said plurality of holes in said first side is aligned with one of said plurality of grooves in said second side;

the depth of each of said plurality of holes extends up to said one of said plurality of grooves; and

each of said holes are sized in a manner so as not to exceed the width of a corresponding groove aligned therewith.

18-24. (canceled)